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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
09/632,388 08/03/2000		Shin Hwa Li	850063.529	1164		
30423	7590 05/06/2002					
STMICROELECTRONICS, INC.			EXAMINER			
	RONICS DRIVE	MALDONADO, JULIO J				
CARROLLT	ON, TX 75006		ART UNIT	PAPER NUMBER		
			2823			
			DATE MAILED: 05/06/2002	DATE MAILED: 05/06/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.

			Applica	tion No.	Applicant(s)	
			09/632,	388	09632388	
	Offic	Action Summary	Examin	er	Art Unit	
ţ.				Maldonado	2823	
Period fo	r Reply				with the correspondence address	
THE I - Exter after - If the - If NO - Failui - Any r	MAILING Ensions of time resions of time resions (6) MONTiperiod for replyers to reply withing ply received by	O STATUTORY PERIOD FO DATE OF THIS COMMUNIC may be available under the provisions of HS from the mailing date of this commit y specified above is less than thirty (30 by is specified above, the maximum state in the set or extended period for reply to by the Office later than three months after adjustment. See 37 CFR 1.704(b).	CATION. of 37 CFR 1.136(a). In no a unication.)) days, a reply within the sl will by statute cause the a	atutory minimum of t will expire SIX (6) M	a reply be timely filed hirty (30) days will be considered timely. ONTHS from the mailing date of this communical ARANDONED (33 U.S.C. § 133)	ation.
1)	Respons	ive to communication(s) file	ed on <u>02/26/2002</u> .			
2a)□	This action	on is FINAL . 2	2b)⊠ This action i	s non-final.		
3) 🗌 Dispositi	Since this closed in on of Clai	accordance with the practi	for allowance exce ce under <i>Ex parte</i>	pt for formal m Quayle, 1935 (natters, prosecution as to the merion 2.D. 11, 453 O.G. 213.	ts is
4)⊠	Claim(s)	<u>1-4,6,7,9,10,20 and 22-27</u> i	s/are pending in the	e application.		
•	4a) Of the	above claim(s) is/ar	e withdrawn from c	onsideration.		
5)	Claim(s) _	is/are allowed.				
6)⊠	Claim(s) <u>1</u>	-4,6,7,9,10,20 and 22-27 is	s/are rejected.			
7)🖂	Claim(s) <u>2</u>	2,4,26 and 27 is/are objecte	d to.			
8)[Claim(s) _	are subject to restrict	ion and/or election	requirement.		
Application	on Papers	;				
9)⊠ 7	he specifi	cation is objected to by the	Examiner.			
10)□ T	he drawin	g(s) filed on is/are:	a) accepted or b)	objected to by	the Examiner.	
	Applicant	may not request that any obje	ction to the drawing(s	s) be held in abe	yance. See 37 CFR 1.85(a).	
11)□ T	he propos	ed drawing correction filed	on is: a) 🔲 :	approved b)	disapproved by the Examiner.	
	If approve	d, corrected drawings are requ	uired in reply to this C	Office action.		
12)∏ T	he oath or	declaration is objected to	by the Examiner.			
Priority u	nder 35 U	.S.C. §§ 119 and 120				
13) 🔲 .	Acknowled	dgment is made of a claim f	or foreign priority u	nder 35 U.S.C	. § 119(a)-(d) or (f).	
a)[☐All b)] Some * c) ☐ None of:				
	1.☐ Cert	tified copies of the priority d	ocuments have be	en received.		
:	2. Cert	ified copies of the priority d	ocuments have be	en received in	Application No	
	á	ies of the certified copies of application from the Internation detailed Office action	tional Bureau (PCT	Rule 17.2(a))		
14) 🗌 Ad	cknowledg	ment is made of a claim for	domestic priority u	nder 35 U.S.C	. § 119(e) (to a provisional applica	ation).
_a)	☐ The tra	anslation of the foreign lang ment is made of a claim fo	uage provisional a	pplication has	been received.	•
Attachment(s)					
2) 🔲 Notice	of Draftspers	es Cited (PTO-892) son's Patent Drawing Review (PT ure Statement(s) (PTO-1449) Pap			v Summary (PTO-413) Paper No(s) f Informal Patent Application (PTO-152)	- ·
6. Patent and Tra FO-326 (Rev			Office Action Summa	arv	Part of Paper No	. 14

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DETAILED ACTION

Specification

The disclosure is objected to because of the following informalities: on page 4, 1. lines 14-18, where the applicant cites, "...8k-20k angstroms...12k angstroms...1.5-8k angstroms...6k angstroms...1k-3k angstroms...3k-6k angstroms..." should cite "...8,000-2,000 angstroms...12,000 angstroms...1,500-8,000 angstroms...6,000 angstroms...1,000-3,000 angstroms...3,000-6,000 angstroms...". On page 4, lines 26-27, where the applicant cites, "...8k-15k angstroms...13k angstroms..." should cite "...8,000-15,000 angstroms...13,000 angstroms...". On page 5, line 3, where the applicant cites, "...2k angstroms..." should cite "...2,000 angstroms..."

Appropriate correction is required.

Claim Objections

Claims 2, 4, 26 and 27 are objected to because of the following informalities: in 2. reference to claim 4 and 26, where the applicant cites, "...2k and 8k angstroms..." should cite "...2,000 and 8,000 angstroms...". In reference to claims 4 and 27, where the applicant cites "...15k angstroms...", should cite "...15,000 angstroms...". Appropriate correction is required.

Claim Rejections - 35 USC § 112

The following is a quotation of the first paragraph of 35 U.S.C. 112: 3.

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

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4. Claims 4 and 27 are rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention. In reference to claim 4, the applicant claims the combined thickness of the oxide layer, the layer of undoped silicate glass, the layer of borophosphorous silicate glass, and the second layer of plasma-enhanced tetraethyl orthosilicate glass is less than approximately 15,000 angstroms, which is larger than the range disclosed on the specification, i.e. 8,000 angstroms to 15,000 angstroms.

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- 5. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 6. Claims 1, 6 and 20 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. In reference to claims 1, 6 and 20 the applicant's claim a planarized layer of plasma-enhanced tetraethyl orthosilicate over at least a portion of the layer of the borophosphorous silicate glass, and <u>not</u> overlying at least a portion of the borophosphorous silicate glass layer, rendering the claims indefinite since the planarized layer of plasma enhanced tetraethyl orthosilicate is deposited all over the borophosphorous silicate glass layer.

Claim Rejections - 35 USC § 103

- 7. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and

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the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

8. Claims 1 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ngo et al. (U.S. 6,127,261) in view of Dawson (U.S. 5,503,882).

In reference to claims 1, 3, 6, 7, 9, 10, 20 and 22-25, Ngo et al. (Fig.1-3) teach a method to form interlayer dielectric layers including a substrate (102); a patterned oxide layer (104) disposed over the substrate (102); a layer of undoped silicate glass (112) disposed over the patterned oxide layer (104); a layer of borophosphorous silicate glass (106) over the layer of undoped silicate glass (112); and a planarized layer of plasmaenhanced tetraethyl orthosilicate (110) over at least a portion of the borophosphorous silicate glass layer (106), the layers of the undoped silicate glass layer (112), the borophosphorous silicate glass layer (106) and the planarized plasma-enhanced tetraethyl orthosilicate layer (110) together forming a pre-metal dielectric layer (column 1, line 29 – column 5, line 15).

Ngo et al. fail to teach forming a second layer of plasma-enhanced tetraethyl orthosilicate overlying the planarized layer of plasma-enhanced tetraethyl orthosilicate layer, directly overlying and being in contact with at least a portion of the borophosphorous silicate glass region having a planar surface. However, Dawson (Fig. 7b) in a related method for planarizing integrated circuit topography teaches the steps of forming a planarized layer of plasma-enhanced tetraethylorthosilicate (42); and a capping layer comprising a second layer of plasma-enhanced tetraethyl orthosilicate (52) overlying the planarized layer of plasma-enhanced tetraethyl orthosilicate layer (42). Therefore, it would have been obvious to one of ordinary skill in the art at the time

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of the invention was made to form the capping layer of Dawson onto the interlayer dielectric structure of Ngo et al. and extend the capping layer in contact with the BPSG, since the capping layer provides a barrier against water sorption into layers below the capping layer (column 9, lines 4-20).

In reference to claims 2, 4, 26 and 27, Ngo et al. in combination with Dawson substantially teach all aspects of the invention but fail to show the layer of borophosphorous silicate glass having a thickness between approximately 2,000 and 8,000 angstroms and the combined thickness of the oxide layer, the layer of undoped silicate glass, the layer of borophosphorous silicate glass, and the second layer of plasma-enhanced tetraethyl orthosilicate glass is less than 15,000 angstroms.

However, the selection of the claimed ranges are obvious because it is a matter of determining optimum process condition by routine experimentation with a limited number of species. In re Jones, 162 USPQ 224 (CCPA 1955)(the selection of optimum ranges within prior art general conditions is obvious) and In re Boesch, 205 USPQ 215 (CCPA 1980)(discovery of optimum value of result effective variable in a known process is obvious).

Response to Arguments

9. Applicant's arguments with respect to claims 1-4, 6, 7, 9, 10, 20 and 22-27 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

10. Papers related to this application may be submitted directly to Art Unit 2823 by facsimile transmission. Papers should be faxed to Art Unit 2823 via the Art Unit 2823

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Fax Center located in Crystal Plaza 4, room 3C23. The faxing of such papers must conform to the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2823 Fax Center number is **(703) 305-3432**. The Art Unit 2823 Fax Center is to be used only for papers related to Art Unit 2823 applications.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **Julio J. Maldonado** at **(703)** 306-0098 and between the hours of 8:00 AM to 4:00 PM (Eastern Standard Time) Monday through Friday or by e-mail via <u>julio.maldonado@uspto.gov</u>. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy, can be reached on (703) 308-4918.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Group 2800 Receptionist** at **(703) 308-0956**.

Julio J. Maldonado
Patent Examiner
Art Unit 2823
703-306-0098
julio.maldonado@uspto.gov

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